

### Applications

- X-band radar

### Product Features

- Frequency Range: 10 – 11GHz
- $P_{SAT}$ : 45.5dBm @  $PIN = 18dBm$
- P1dB: 41dBm @ Midband
- PAE: >47% @  $PIN = 18dBm$
- Large Signal Gain: 27.5dB
- Small Signal Gain: 35dB
- Bias:  $V_D = 28V$ ,  $I_{DQ} = 290mA$ ,  $V_G = -2.7V$  Typical
- Pulsed  $V_D$ :  $PW = 100\mu s$  and  $DC = 10\%$
- Chip Dimensions: 5.0 x 4.86 x 0.10 mm

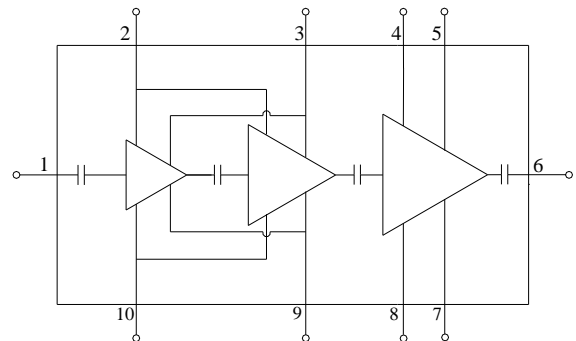
### General Description

TriQuint's TGA2623 is an x-band, high power MMIC amplifier fabricated on TriQuint's production 0.25um GaN on SiC process. The TGA2623 operates from 10 – 11GHz and provides a superior combination of power, gain and efficiency. Achieving 35W of saturated output power with 27.5dB of large signal gain and 47% power-added efficiency, the TGA2623 provides the level of performance demanded by today's system architectures. Depending on the system requirements, the TGA2623 can support cost saving initiatives on existing systems while supporting next generation systems with increased performance.

Lead-free and RoHS compliant.

Evaluation boards are available upon request.

### Functional Block Diagram



### Pad Configuration

Pad No.	Symbol
1	RF In
2, 10	$V_{G1-2}$
4, 8	$V_{G3}$
3, 9	$V_{D1-2}$
5, 7	$V_{D3}$
6	RF Out

### Ordering Information

Part	ECCN	Description
TGA2623	3A001.b.2.b	10 – 11GHz 35W GaN Power Amplifier

### Absolute Maximum Ratings

Parameter	Value
Drain Voltage ( $V_D$ )	40V
Gate Voltage Range ( $V_G$ )	-10 to -2V
Drain Current ( $I_{D1-2}$ )	2.3A
Drain Current ( $I_{D3}$ )	4.3A
Gate Current ( $I_{G1-2}$ )	-3.5 to 17.5mA
Gate Current ( $I_{G3}$ )	-11 to 28mA
Power Dissipation ( $P_{DISS}$ ), 85°C, CW	96W
Input Power ( $P_{IN}$ ), CW, 50Ω, $V_D = 28V$ , 85°C	24dBm
Input Power ( $P_{IN}$ ), CW, VSWR 6:1, $V_D = 28V$ , 85°C	20dBm
Channel Temperature ( $T_{CH}$ )	275°C
Mounting Temperature (30 seconds)	320°C
Storage Temperature	-55 to 150°C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

### Recommended Operating Conditions

Parameter	Value
Drain Voltage ( $V_D$ )	28V
Drain Current ( $I_{DQ}$ )	290mA (Total)
Gate Voltage ( $V_G$ )	-2.7V (Typ.)

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

### Electrical Specifications

Test conditions unless otherwise noted: 25°C,  $V_D = 28V$ ,  $I_{DQ} = 290mA$ ,  $V_G = -2.7V$  Typical, Pulsed  $V_D$ . PW = 100us, DC = 10%

Parameter	Min	Typical	Max	Units
Operational Frequency Range	10		11	GHz
Small Signal Gain		35		dB
Input Return Loss		>15		dB
Output Return Loss		>10		dB
Power Gain ( $P_{in} = 18dBm$ )		27.5		dB
Output Power ( $P_{in} = 18dBm$ )		45.5		dBm
Power Added Efficiency ( $P_{in} = 18dBm$ )		>47		%
Power @ 1dB Compression ( $P_{1dB}$ )		41 @ Midband		dB
Small Signal Gain Temperature Coefficient		-0.075		dB/°C
Recommended Operating Voltage:	20	28	32	V

### Thermal and Reliability Information

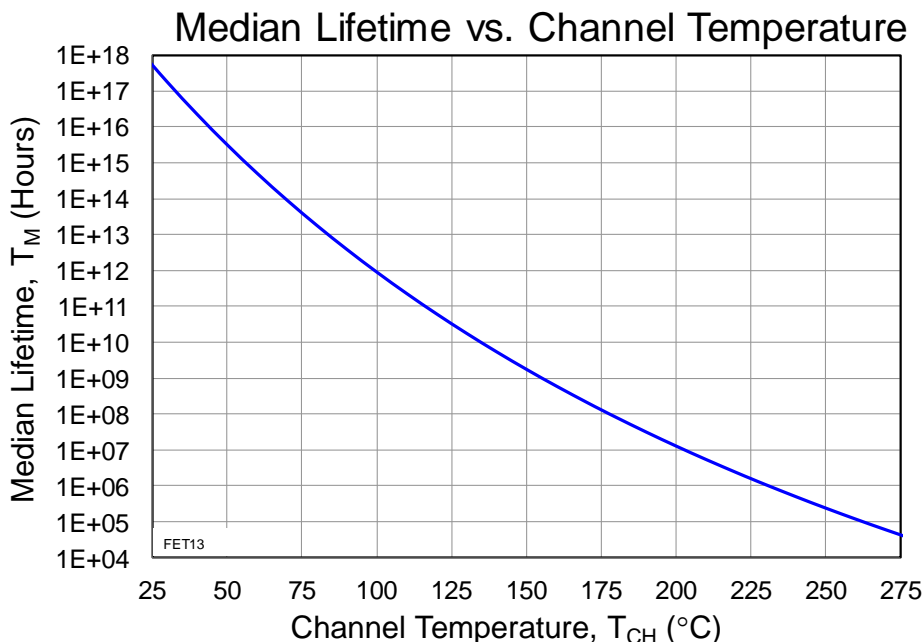
Parameter	Test Conditions	Value	Units
Thermal Resistance ( $\theta_{JC}$ ) <sup>(1)</sup>	$T_{base} = 85^{\circ}C$ , Pulsed $V_D$ : PW = 100us, DC = 10%	1.14	$^{\circ}C/W$
Channel Temperature ( $T_{CH}$ ) (Under RF drive)	$T_{base} = 85^{\circ}C$ , $V_D = 28V$ , $I_{D\_Drive} = 3A$ ,	143	$^{\circ}C$
Median Lifetime ( $T_M$ )	$P_{IN} = 22dBm$ , $P_{OUT} = 45.3dBm$ , $P_{DISS} = 51W$	$3.85 \times 10^{10}$	Hrs
Thermal Resistance ( $\theta_{JC}$ ) <sup>(1)</sup>	$T_{base} = 85^{\circ}C$ , CW	1.97	$^{\circ}C/W$
Channel Temperature ( $T_{CH}$ ) (Under RF drive)	$T_{base} = 85^{\circ}C$ , $V_D = 28V$ , $I_{D\_Drive} = 2.94A$ ,	187	$^{\circ}C$
Median Lifetime ( $T_M$ )	$P_{IN} = 22dBm$ , $P_{OUT} = 44.9dBm$ , $P_{DISS} = 52W$	$4.12 \times 10^7$	Hrs

Notes:

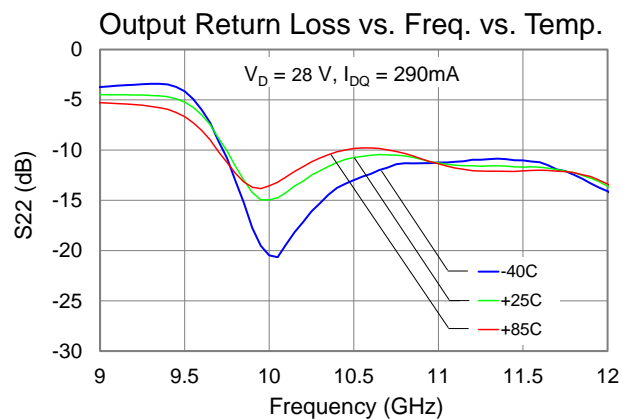
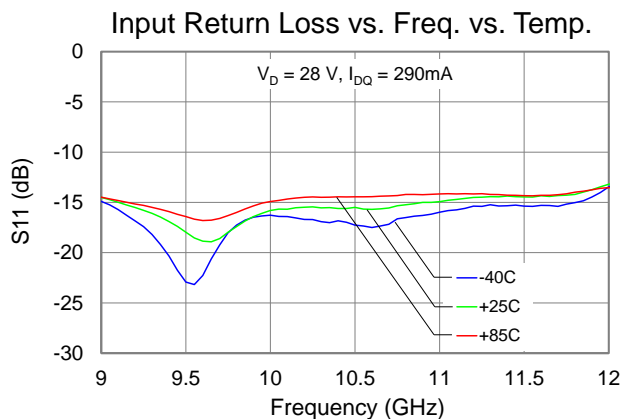
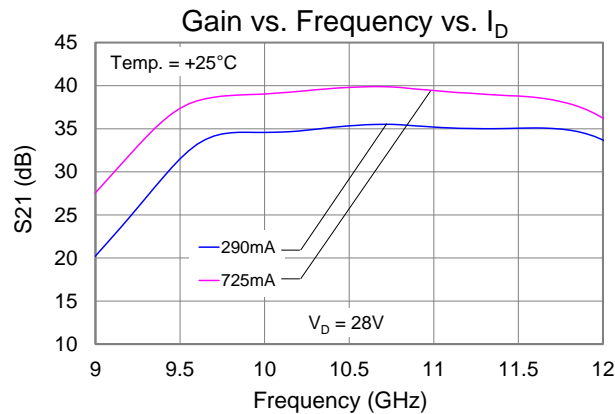
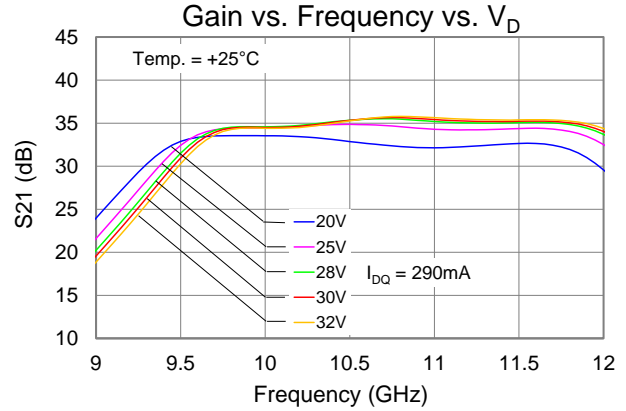
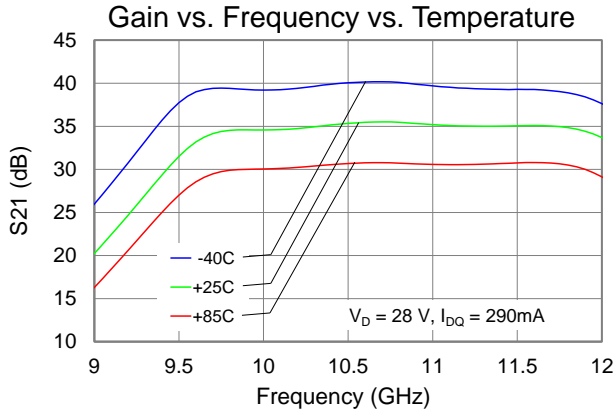
1. Thermal resistance measured to back of carrier plate. MMIC mounted on 40 mils CuM0 (80/20) carrier using 1.5 mil AuSn.

### Median Lifetime

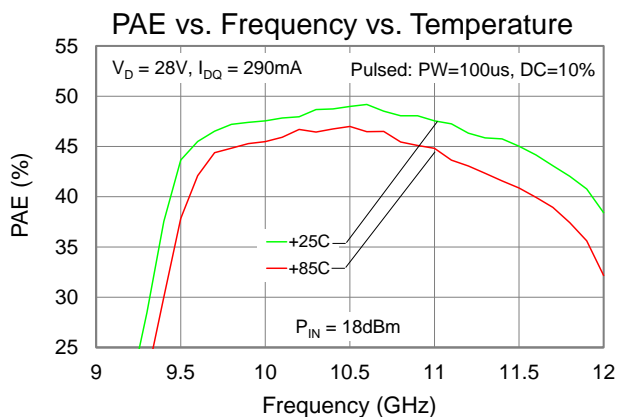
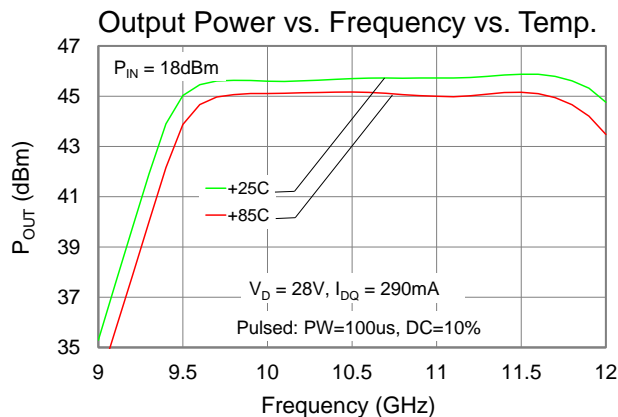
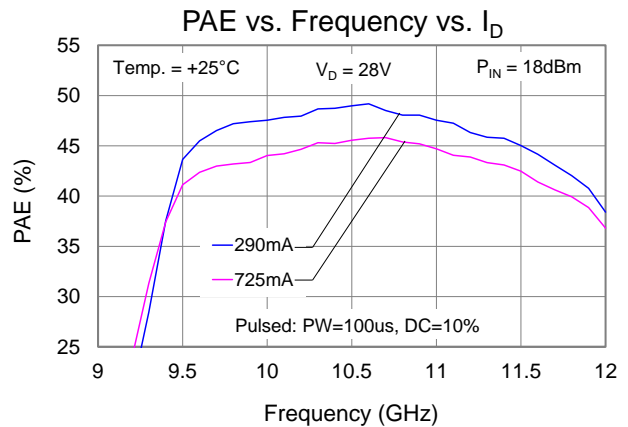
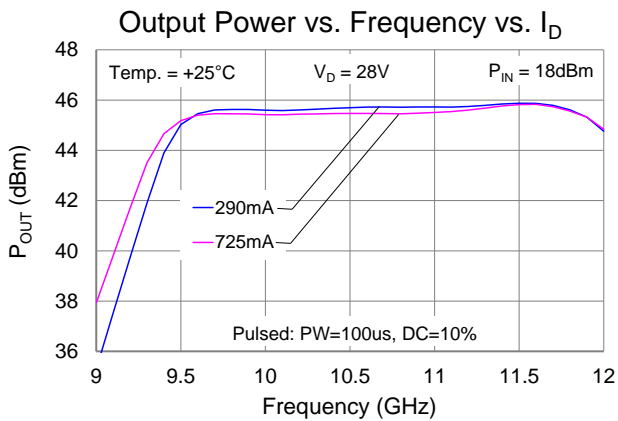
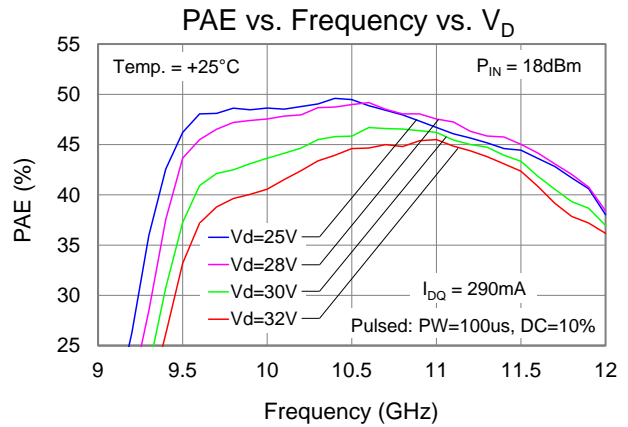
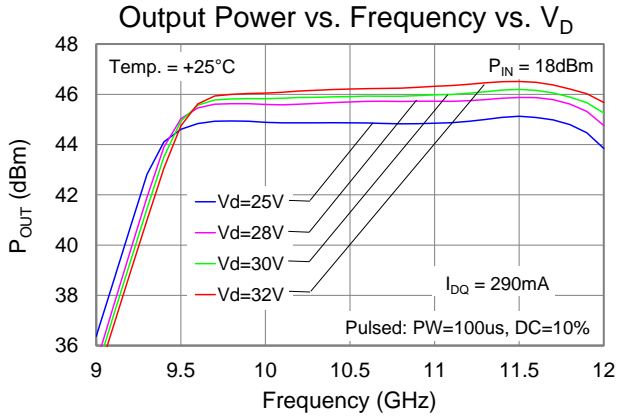
Test Conditions:  $V_D = 40 V$ ; Failure Criteria = 10% reduction in  $I_{D\_MAX}$



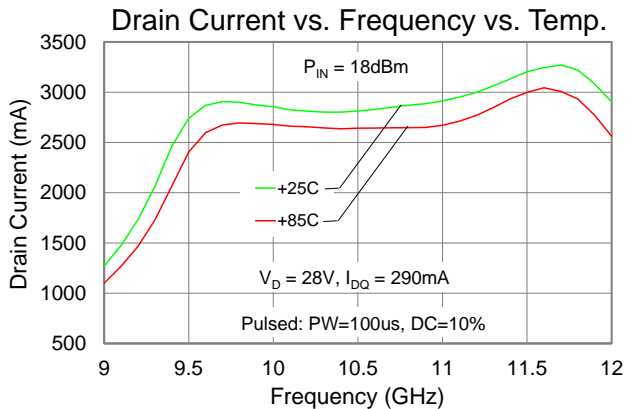
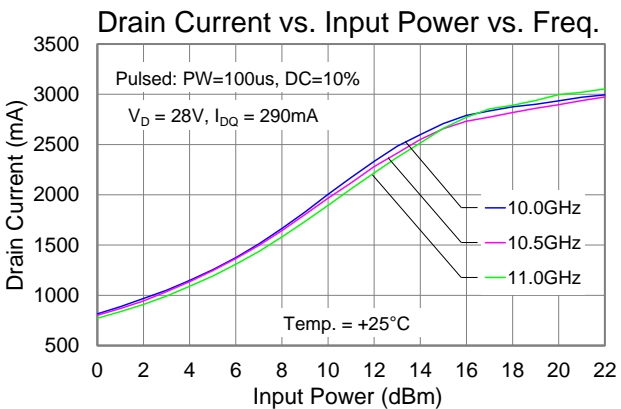
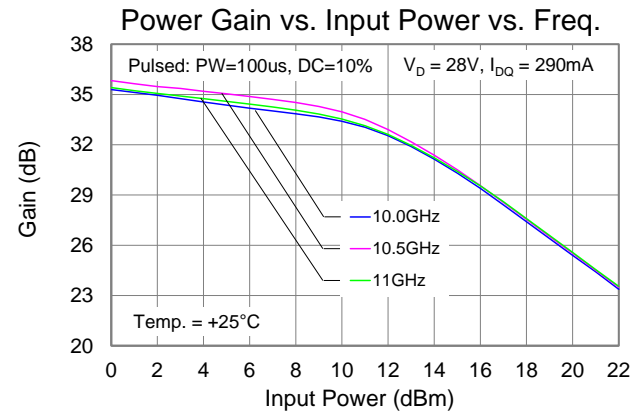
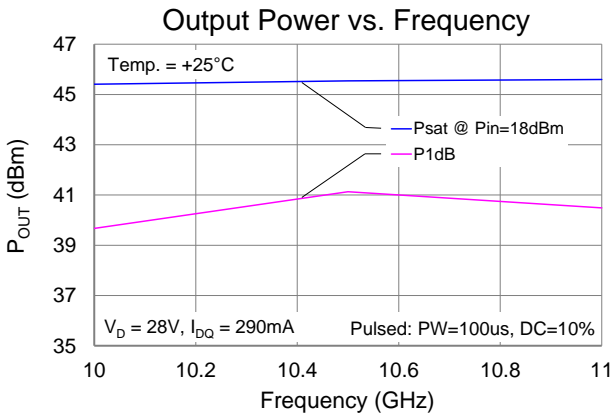
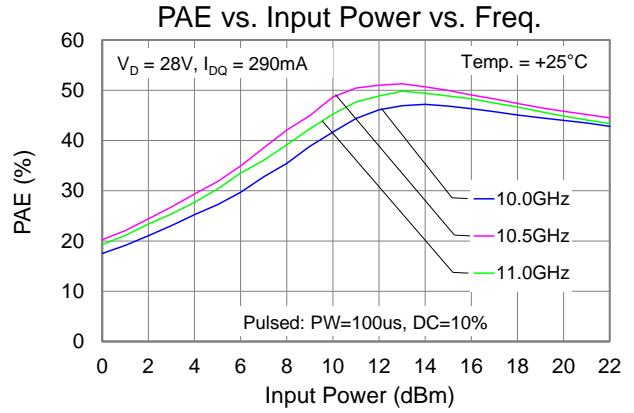
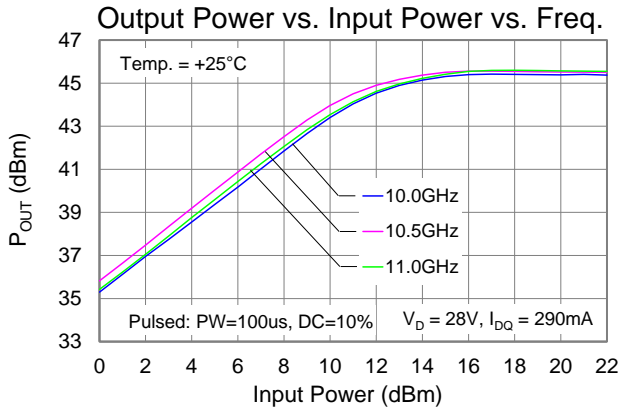
**Typical Performance (Small Signal)**



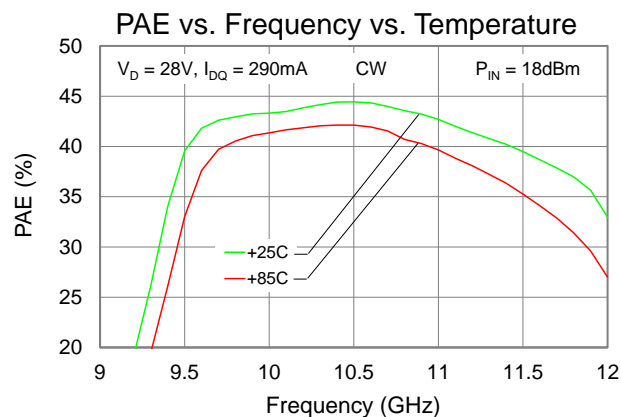
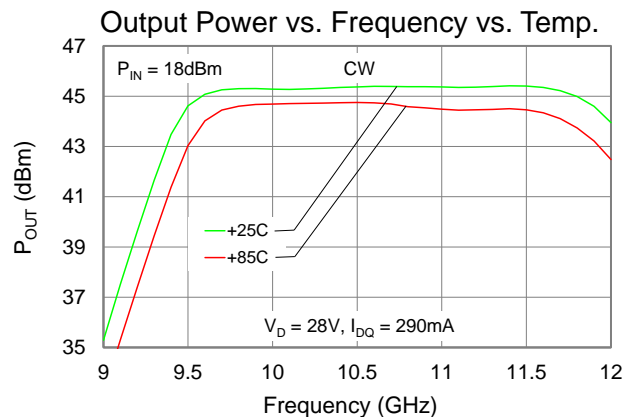
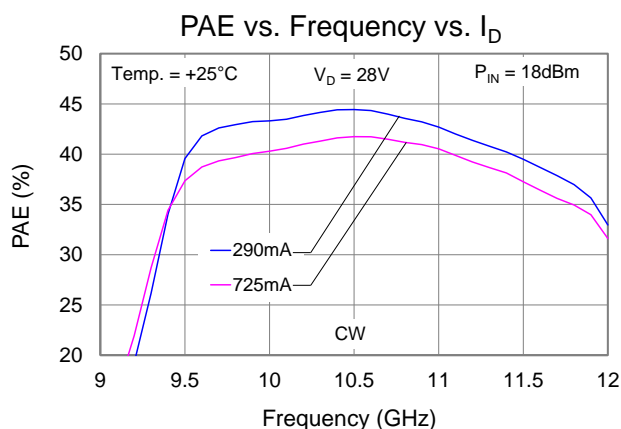
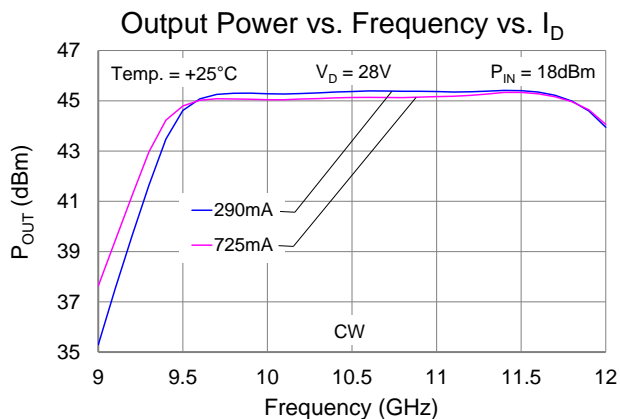
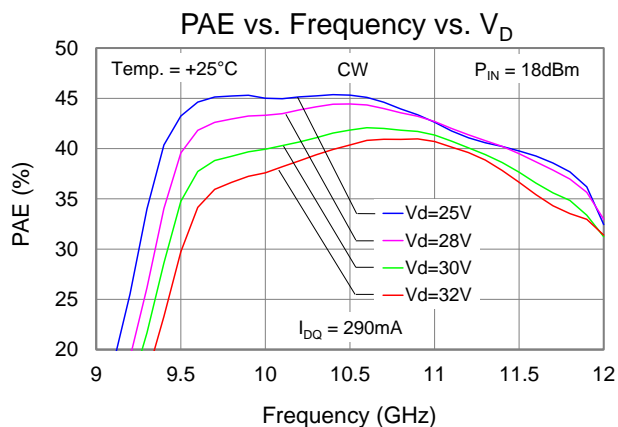
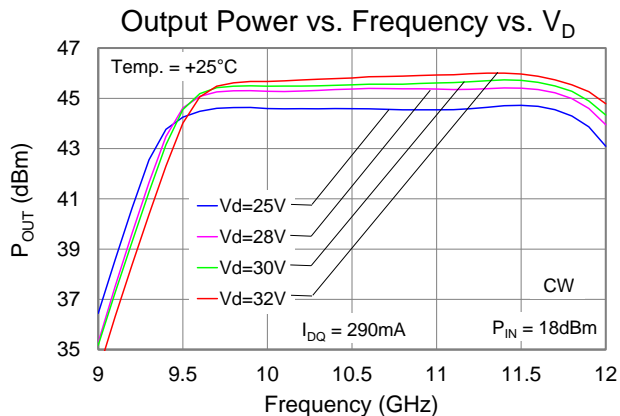
**Typical Performance (Pulsed Operation)**



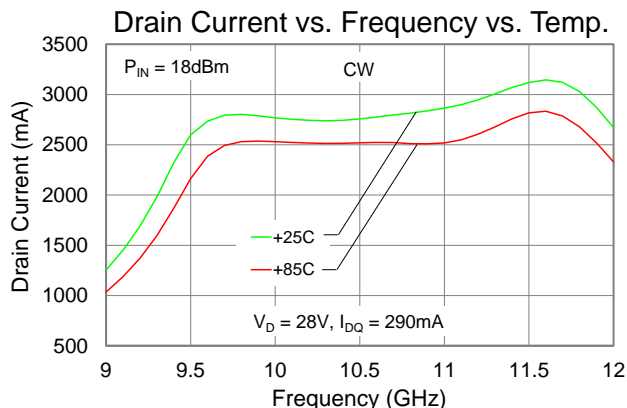
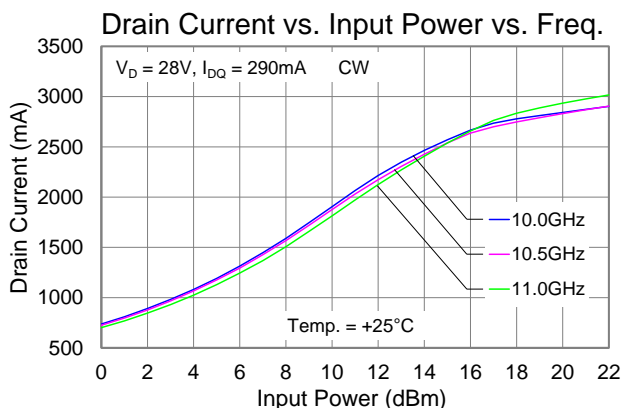
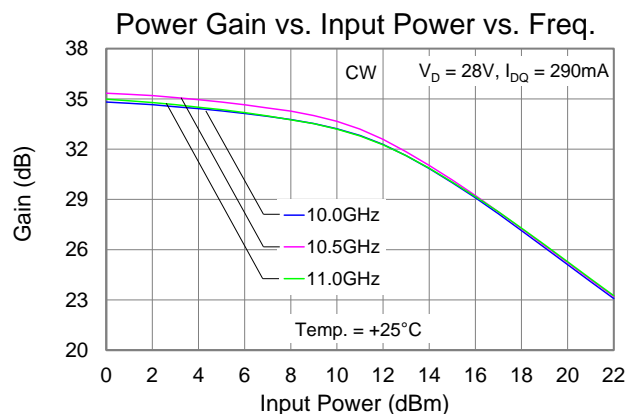
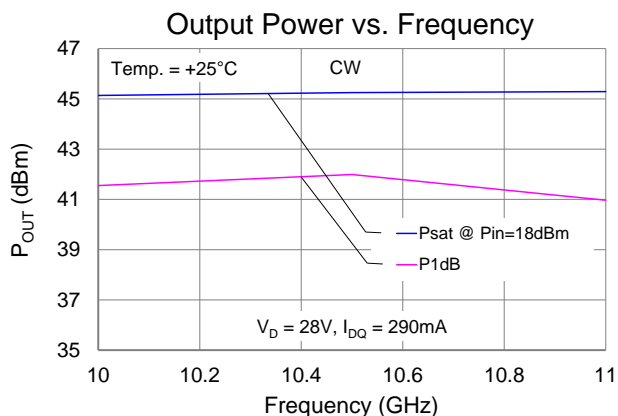
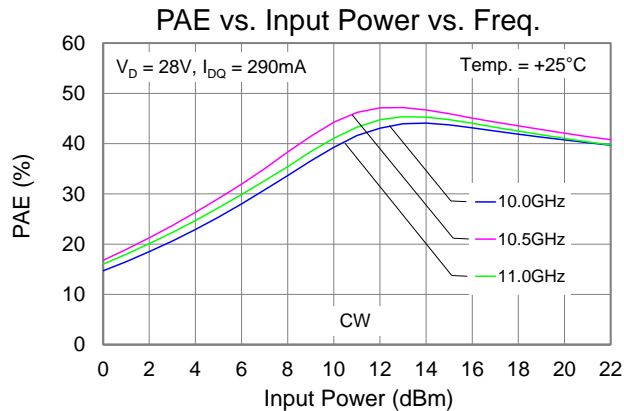
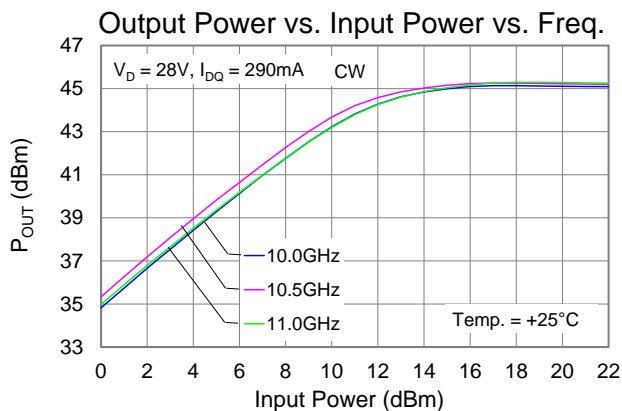
### Typical Performance (Pulsed Operation)



**Typical Performance (CW Operation)**

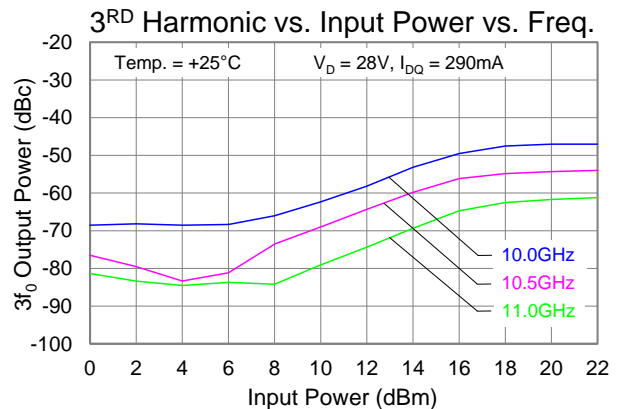
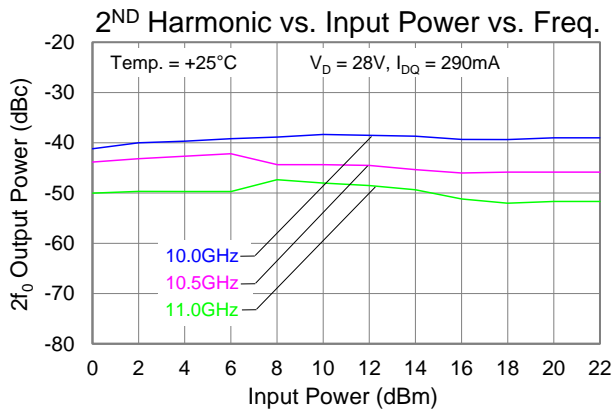
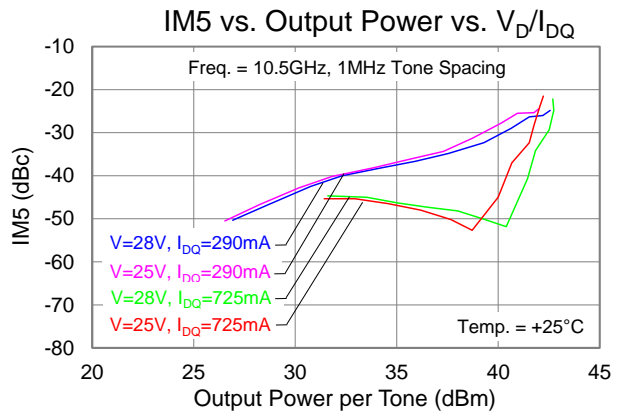
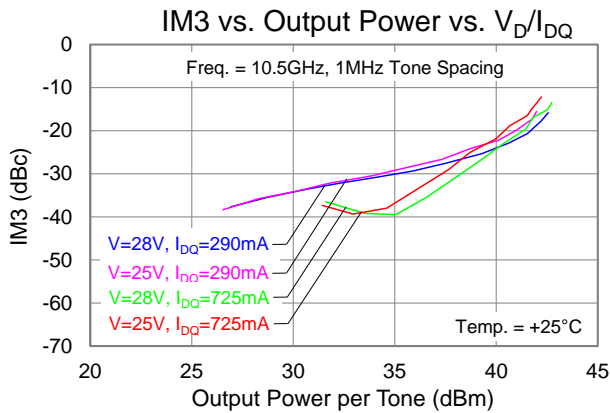
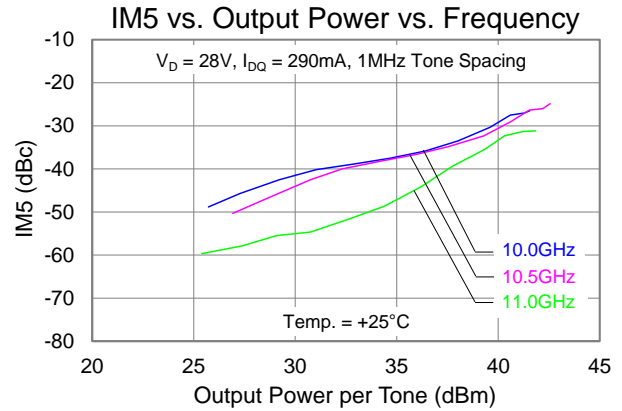
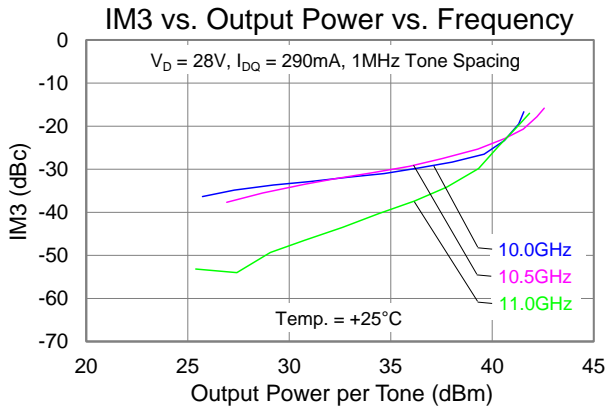


### Typical Performance (CW Operation)

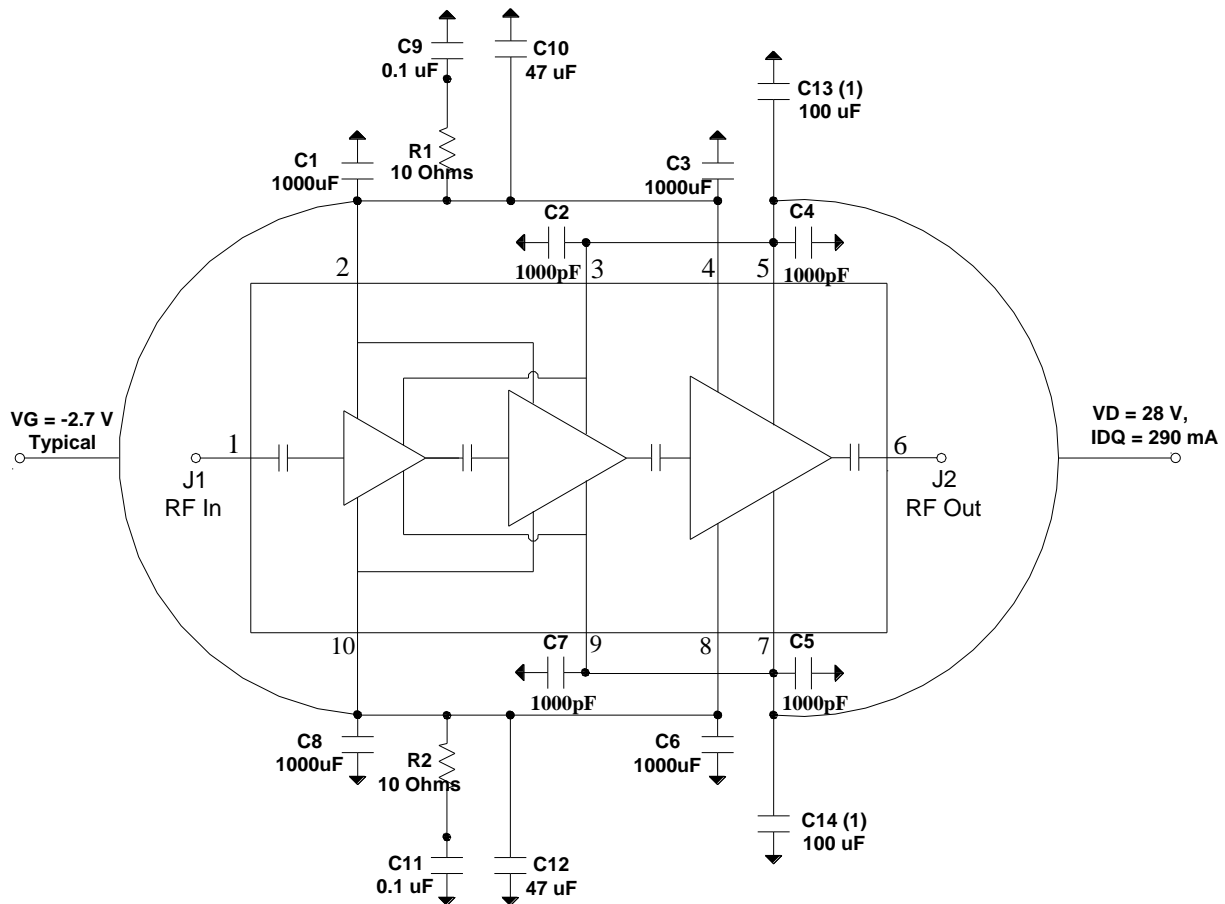




### Typical Performance (Linearity)



### Application Circuit



#### Notes:

1. Remove caps for pulse operation. These caps are part of the cable harness for CW operation.

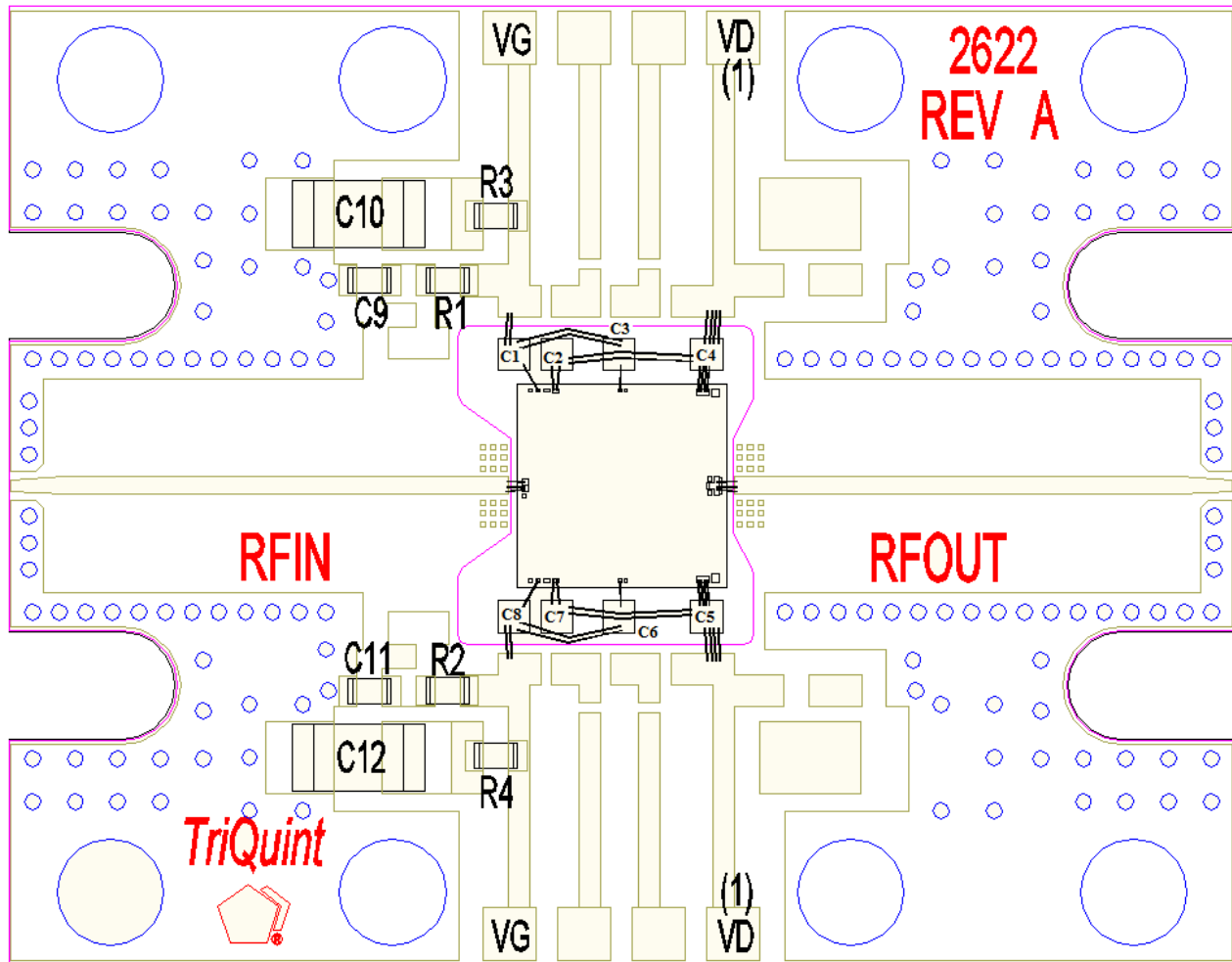
#### Bias-up Procedure

1. Set  $I_D$  limit to 3.5A,  $I_G$  limit to 10mA
2. Set  $V_G$  to -5.0V
3. Set  $V_D$  +28V
4. Adjust  $V_G$  more positive until  $I_{DQ} = 290\text{mA}$  ( $V_G \sim -2.7\text{V}$  Typical)
5. Apply RF signal

#### Bias-down Procedure

1. Turn off RF signal
2. Reduce  $V_G$  to -5.0V. Ensure  $I_{DQ} \sim 0\text{mA}$
3. Set  $V_D$  to 0V
4. Turn off  $V_D$  supply
5. Turn off  $V_G$  supply

## Evaluation Board (EVB) Layout Assembly



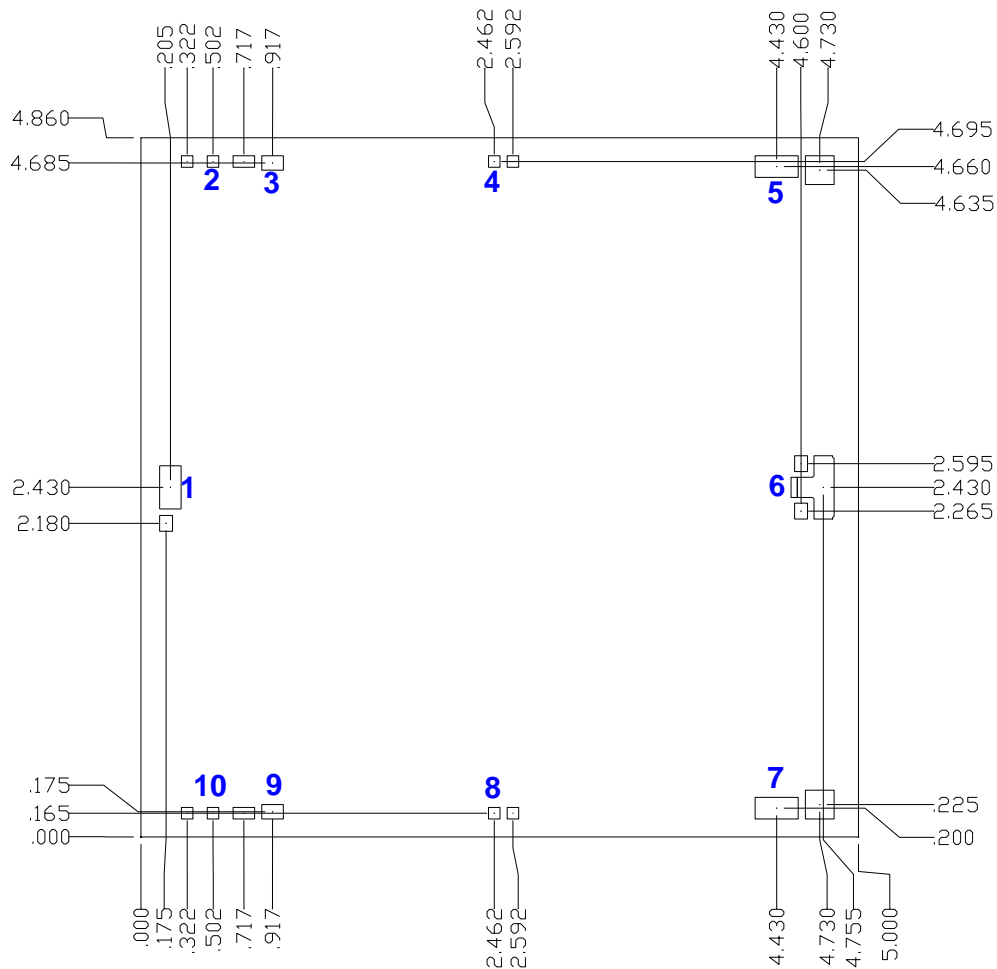
Notes:

1. 100uF/100V charge storage cap is needed on the drain. For pulsed operation this cap must be on the supply-side of the pulse-modulator.

### Bill of Materials

Reference Design	Value	Description	Manufacturer	Part Number
C1 – C8	1000pF	SLC, 50V	Various	
C9, C11	0.1uF	Cap, 0402, 50V, 10%, X7R	Various	
C10, C12	47uF	Cap, 1206, 50V, 10%, X7R	Various	
R1 – R2	10Ω	Res, 0402	Various	
R3 – R4	0Ω	Res, 0402	Various	

### Mechanical Drawing & Bond Pad Description



Unit: millimeters  
 Thickness: 0.10  
 Die x, y size tolerance: +/- 0.050  
 Chip edge to bond pad dimensions are shown to center of pad  
 Ground is backside of die

Bond Pad	Symbol	Pad Size	Description
1	RF In	0.150 x 0.300	RF Input; matched to 50Ω
2, 8	VG1-2	0.080 x 0.080	Gate voltage 1, bias network is required; see Application Circuit on page 10 as an example.
4, 10	VG3	0.080 x 0.080	Gate voltage 3, bias network is required; see Application Circuit on page 10 as an example.
3, 9	VD1-2	0.150 x 0.100	Drain voltage 1, bias network is required; see Application Circuit on page 10 as an example.
5, 7	VD3	0.300 x 0.150	Drain voltage 3, bias network is required; see Application Circuit on page 10 as an example.
6	RF Out	0.140 x 0.400	RF Output; matched to 50Ω

## Assembly Notes

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment (i.e. epoxy) can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.

Reflow process assembly notes:

- Use AuSn (80/20) solder and limit exposure to temperatures above 300°C to 3-4 minutes, maximum.
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- Do not use any kind of flux.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonic are critical parameters.
- Aluminum wire should not be used.
- Devices with small pad sizes should be bonded with 0.0007-inch wire.

**Product Compliance Information****ESD Sensitivity Ratings**

Caution! ESD-Sensitive Device

ESD Rating: TBD  
Value: TBD  
Test: Human Body Model (HBM)  
Standard: JEDEC Standard JESD22-A114

**ECCN**

US Department of Commerce: 3A001.b.2.b

**Solderability**

This part is compliant with EU 2002/95/EC RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- PFOS Free
- SVHC Free

**Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations, and information about TriQuint:

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For technical questions and application information: Email: [info-products@triquint.com](mailto:info-products@triquint.com)

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### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

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